A microscopic view of a silicon chip with a lens above it. The chip surface is covered in intricate patterns of metal and silicon, with various structures and connections visible. The lens is positioned in the upper center, focusing on a specific area of the chip.

# Single Chip Analog RF Memory & Spectral Imager, ARFM

RF Time & Frequency Domain Snapshots Captured  
with CMOS Single Chip Spectral Imager

“Spectrum Analyzer on a Chip”

# Single Chip ARFM Time & Spectral Domain Imager

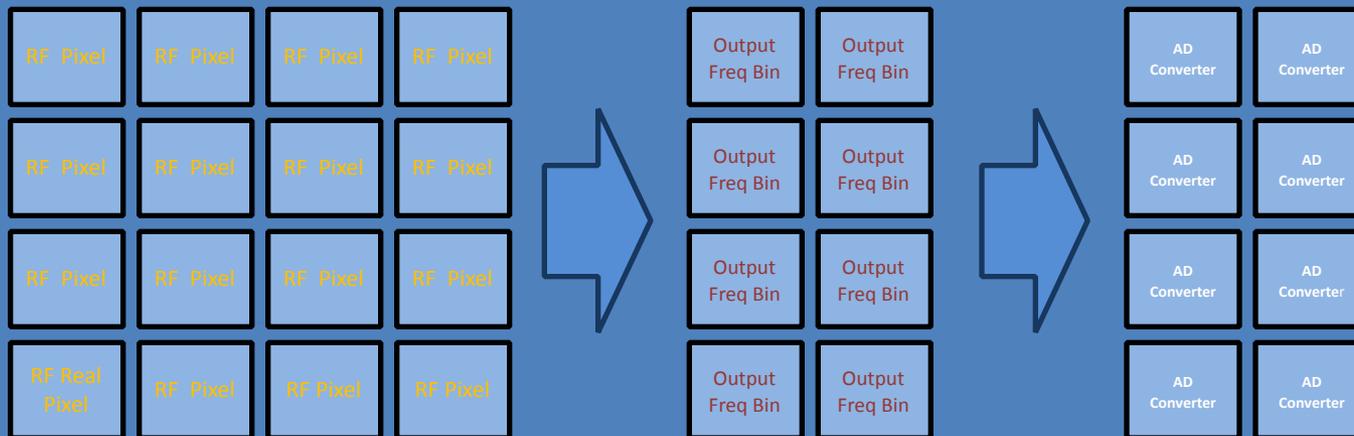
## Utilize Digital Imaging Sensor/DRAM Technology

- Employ Large CMOS Sensor Device Arrays
  - Sensor Configured
    - “N<sub>c</sub>” Columns
    - “N<sub>row</sub>” Rows
    - N Array Size = N<sub>c</sub>\*N<sub>row</sub>
  - Signal Input
    - Applied to each Column via NMOS switch
      - » Column Sequentially Addressed in Time
      - » Stores Signal Input *Current* on **RF Pixel** Column NMOS Device
        - Behaves like N *Current Mode* Sample and Holds
    - Step to next Column when previous Column full
- Captures RF Time Domain
  - Discrete Time Continuous Amplitude
  - N Time Samples
  - N\*ts = Total Capture Time Slot
- Large Number of **RF Pixels**
  - Limited by Chip Size
    - Greater than 100K Pixels
      - » 10u by 10u CMOS (Example)
- High RF Sample Rates
  - Limited by Clock/Switch Speed
    - Improves with Silicon Feature Size Reduction
- Large RF “Image” Capture Time
  - Limited by Chip Size
    - Improves with RF Pixel Number
  - Limited (long end) by NMOS Device Gate Charge Hold Time
    - Dictated by Process Node
    - Limited by Leakage
    - Partial Leakage Compensation Possible

Enables Large Array Single Chip RF Time Domain Signal Capture

# Notional 4 By 4 Example: Single Chip RF Imager

## Example CMOS 4 By 4 *RF Pixel* Array (N=16)



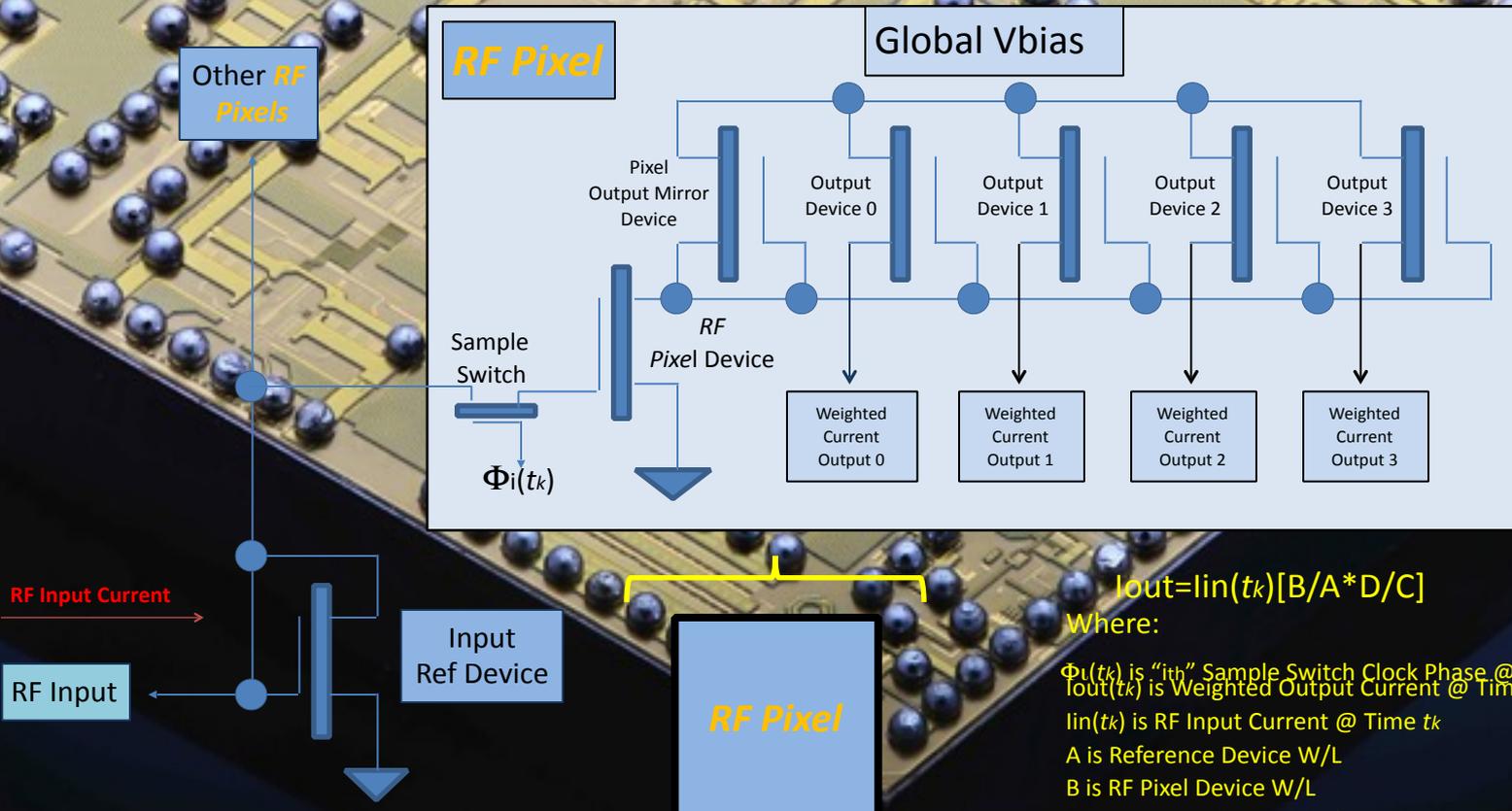
Digital Clock Generator

Digital I/O Interface

Support Electronics

# “RF Pixel” Circuit Concept

## Input RF Pixel



$$I_{out} = I_{in}(t_k) [B/A * D/C]$$

Where:

$\Phi_i(t_k)$  is “ith” Sample Switch Clock Phase @ Time  $t_k$   
 $I_{out}(t_k)$  is Weighted Output Current @ Time  $t_k$

$I_{in}(t_k)$  is RF Input Current @ Time  $t_k$

A is Reference Device W/L

B is RF Pixel Device W/L

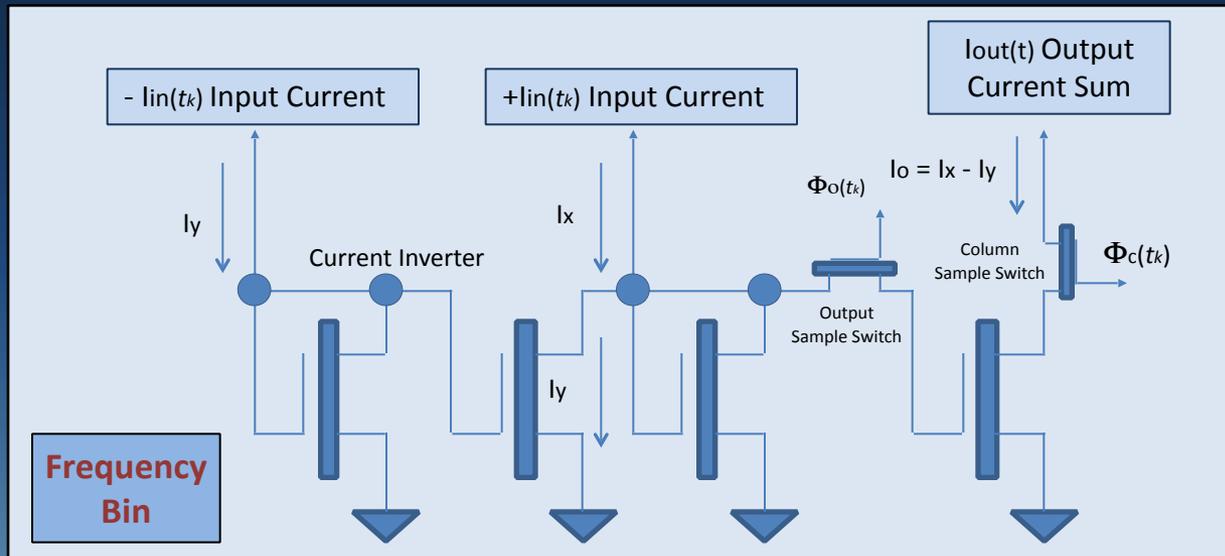
C is Output Ref Device W/L

D is Mirror Device W/L

# Spectral Image Analog FFT

## “Frequency Bin” Circuit Concept

### Output Current Summation *Frequency Bin*



**Output  
Frequency Bin**

$$i_{out}(t) = \sum +i_{in}(t_k) - \sum -i_{in}(t_k)$$

Where:

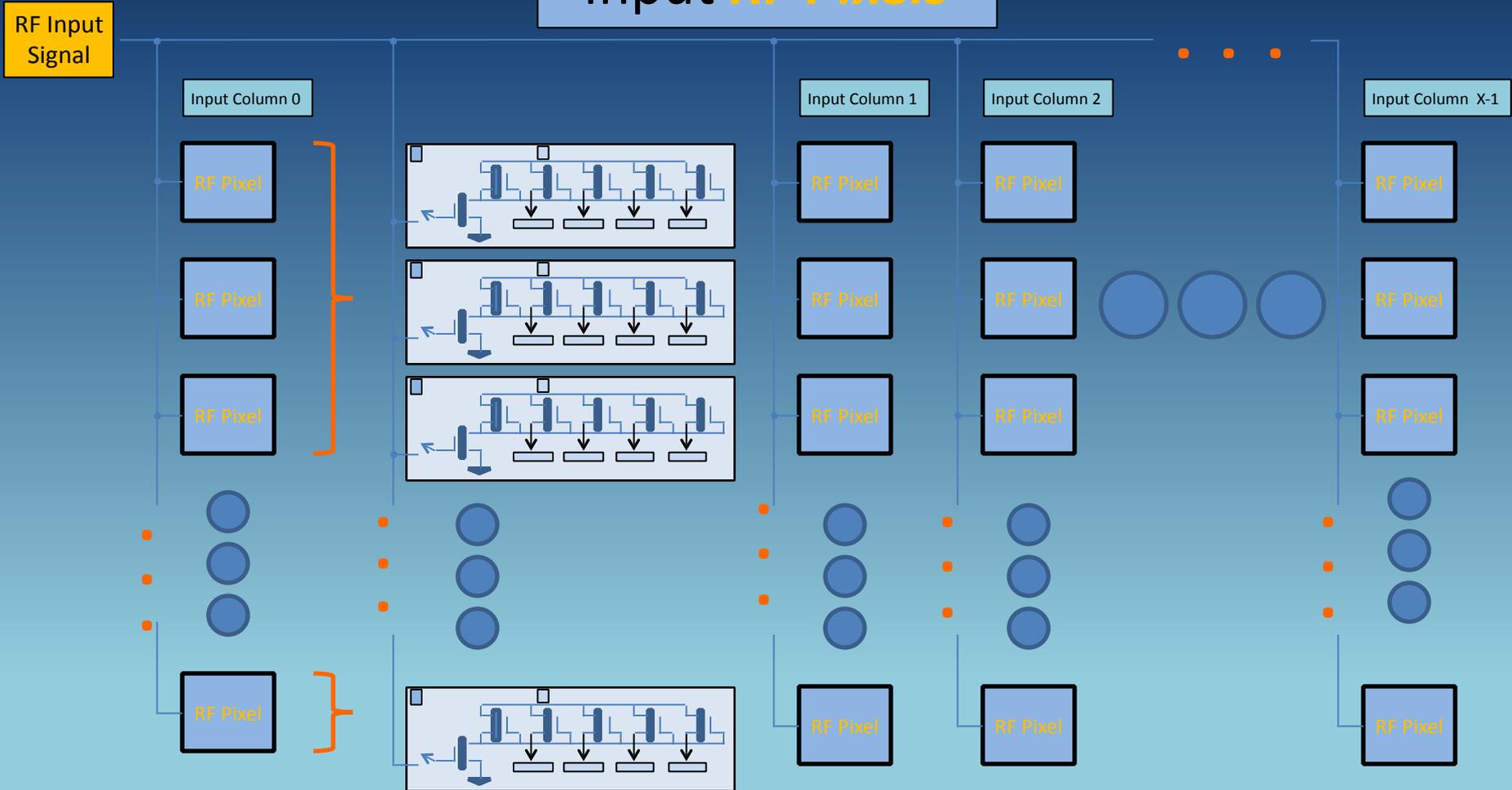
$i_{out}(t_k)$  is Weighted Sum Output Current

$+i_{in}(t_k)$  is Added Input Current

$-i_{in}(t_k)$  is Subtracted Input Current

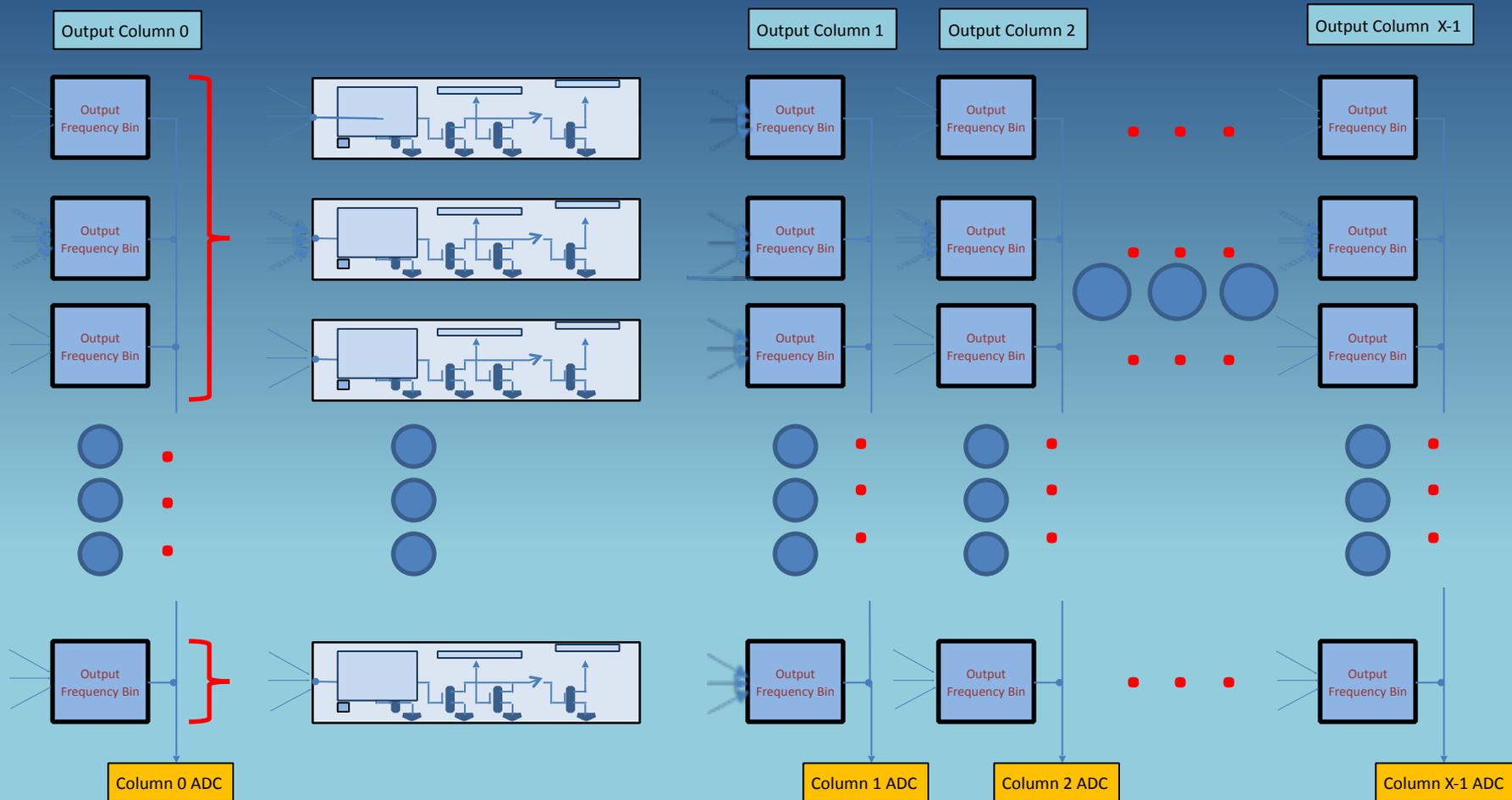
# Single Chip ARFM Time Capture

Input *RF Pixels*



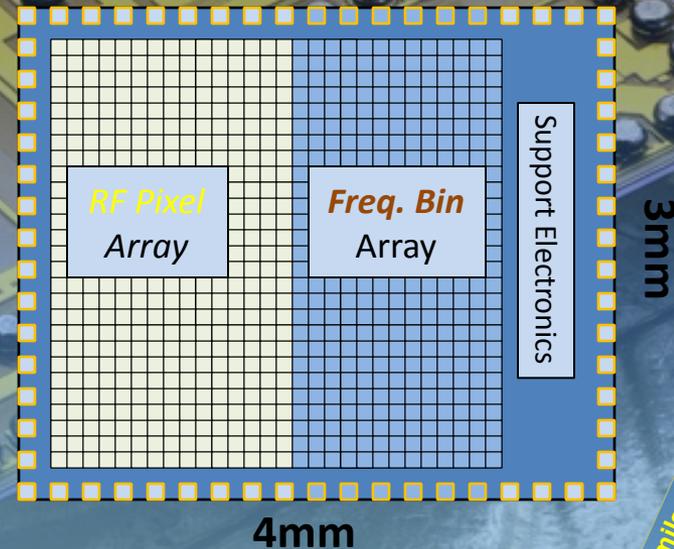
# Single Chip ARFM Spectral Image

## Output Current Summation *Frequency Bins*



# Example Single Chip 10K RF Pixel ARFM Time & Spectral Domain Imager

- **Example Chip: 10K RF Pixel**, DC-5GHz, @ 1MHz Res. with 1us RF Spectral Image Capture
  - 4mm by 3mm CMOS Chip Size
    - 100 by 100 X & Y Array
      - 10u by 10u **RF Pixel** Size
        - » NMOS Sample Device
    - 10GSPS Sample Rate
      - 1us Total RF Time Image Capture
        - » 10ns per Column
      - DC-5GHz Nyquist Frequency Span
        - » 1MHz Frequency Resolution
    - 10 Bit Analog to Digital Conversion
      - One AD Converter per Column
        - » 100 Total
  - **Input Clocking**
    - Single Input Clock Reference
    - **RF Pixel** Sample Clock Derived
      - Each Column Delay/Phase Locked
    - Column ADC
      - Delay/Phase Locked
    - Output Clock
      - Delay/Phase locked
  - **Single 2.7 Volt Supply**
    - On Chip Low Drop Out Regulators
    - Higher Efficiency with separate 1.2v Digital Supply
  - **Digital Interface**
    - 100 10 Bit AD Converter
    - 10K 10 Bit Words
    - High Speed Digital Data Outputs
      - Advanced FPGA Compatible
      - Advanced DSP Compatible



Example **10K** CMOS Chip